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# TND6275/D

## RF Transceiver Reference Design Tuned for 915 MHz Using Wireless MCU AXM0F243



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### REFERENCE DESIGN OVERVIEW

#### Introduction

This reference design contains a compact and efficient reference design for the AXM0F243 that demonstrates its operation in the European 915 MHz ISM band. By using the design detailed below to implement the AXM0F243, it is intended that the time and risk associated with designing and certifying a final product can be greatly reduced.

The source design and fabrication files can be downloaded from the DVK-AXM0F243-915-x-GEVK web page located at [www.onsemi.com](http://www.onsemi.com).

#### Design Schematic Overview

### REFERENCE DESIGN

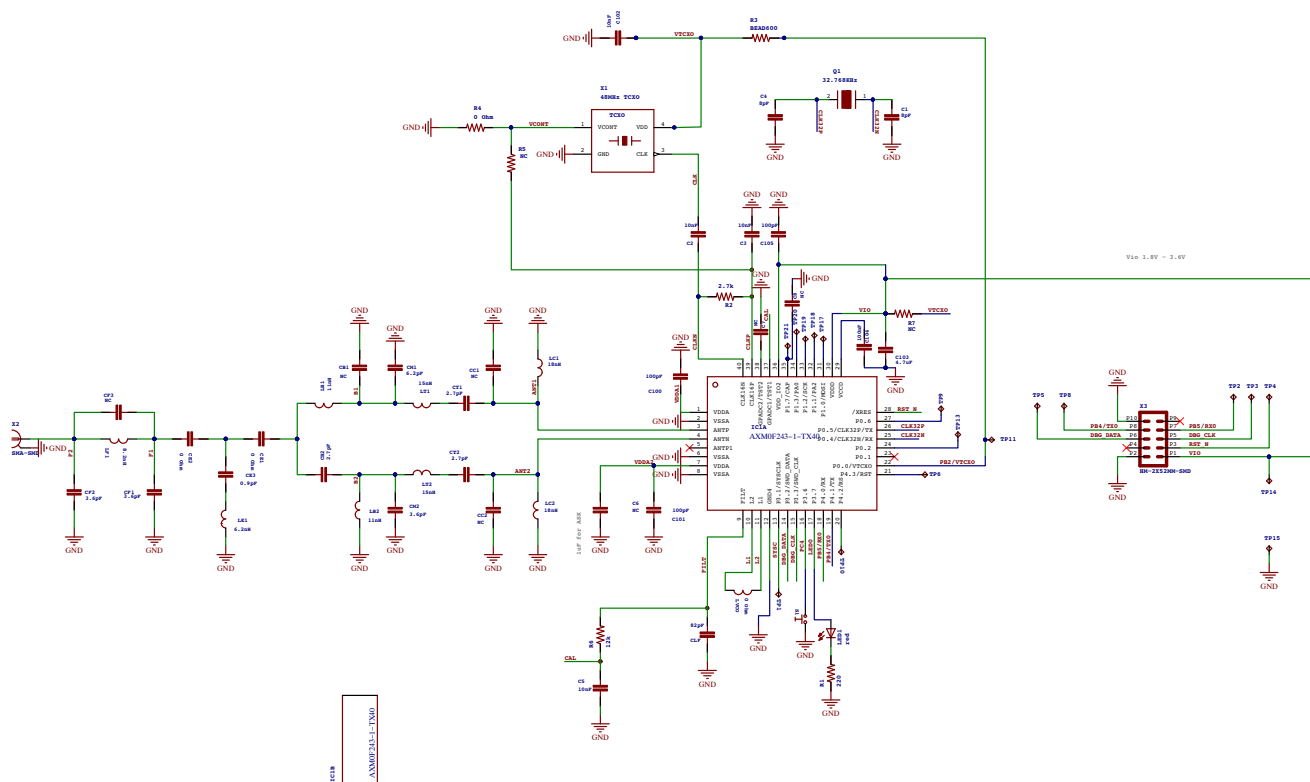


Figure 1. Design Schematic Overview

**Class-E Amplifier and Match Network**

The AXM0F243 utilizes a class-E power amplifier, which includes components both internal and external to the IC. For this reason, the selection of component values between ANTP / ANTEN and the antenna is not merely an impedance matching problem, but an amplifier design problem as well. This network must be tuned to the desired operating frequency for proper RF performance. Reference designs, including this one, have been provided by ON Semiconductor for commonly used frequencies. For additional details on tuning this network to different frequencies, see the References section at the end of this document. Note that typically this network is designed for optimal TX performance, and the frequency and gain

tracking loops in the receiver will compensate to maintain the optimum RX sensitivity.

The network used in this design is shown in greater detail below. The components LC1/2, CC1/2, CT1/2, LT1/2, and CM1/2 are part of the class-E amplifier. CB1/2 and LB1/2 form a balun, and are used to transform the differential signal to single-ended. CE1/2/3, LE1, CF1/2/3, and LF1 are components of harmonic filters used to achieve an output spectrum that is compliant with regulations.

The values for 915 MHz are shown in the following image, as well as the bill-of-materials below. Note that the components labeled “NC” are not necessary and can be removed for applications at this frequency.

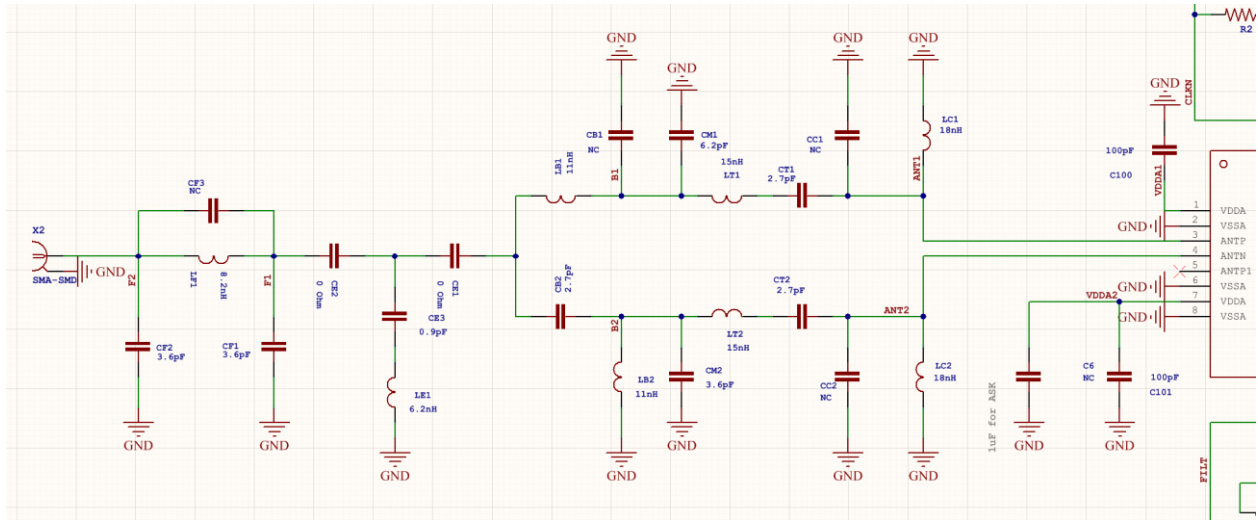


Figure 2.

# TND6275/D

## TCXO and Optional Crystal

In order to achieve stable RF performance over temperature, a 48 MHz TCXO is employed as a clock reference. This clock is connected internally to the radio transceiver core, but can also be made available to the

M0+ MCU core with software configuration. There is also an optional 32.768 kHz crystal that connects directly to the MCU core. The schematic for these components is shown in detail below:

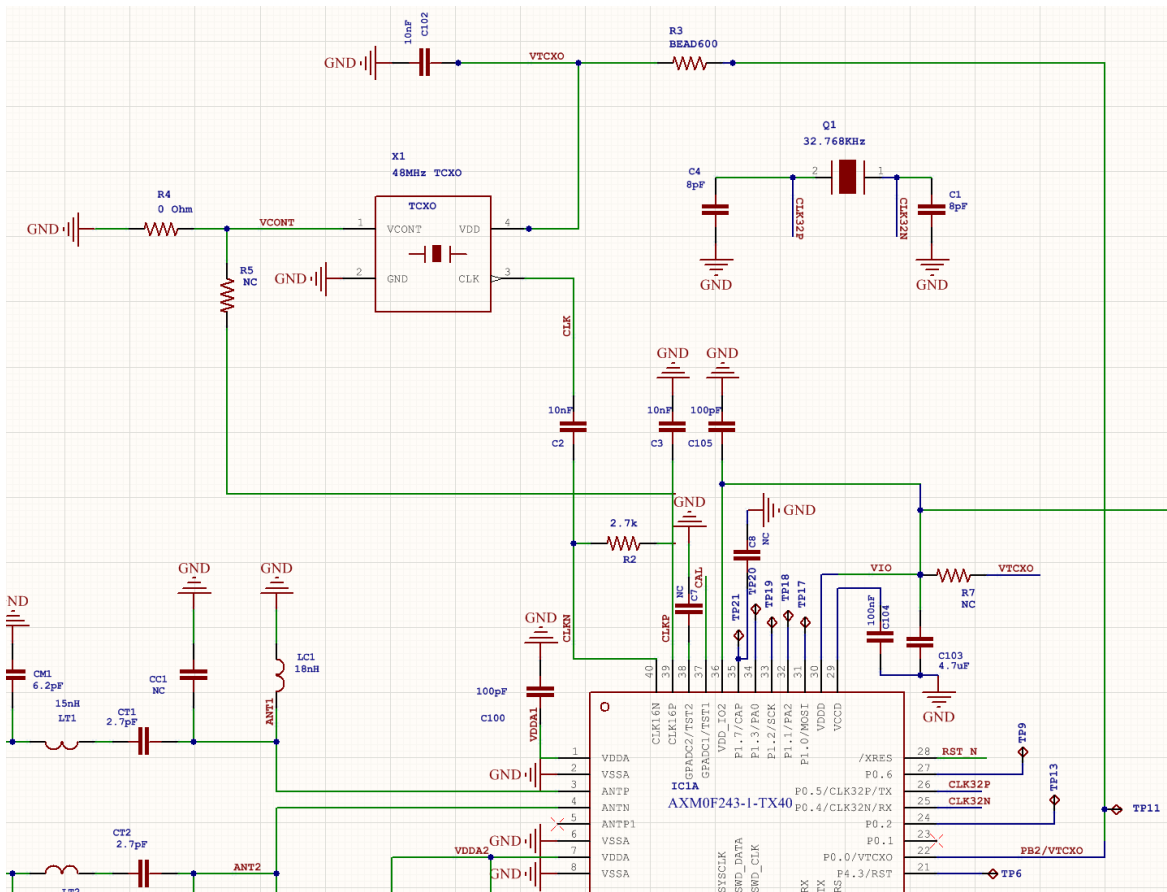


Figure 3.

# TND6275/D

## VCO Calibration Hardware

In order to optimize the phase noise of the RF synthesizer, an optional VCO current calibration algorithm has been included in easyAX5043.c – a library that is used by

AX-RadioLab. In order to utilize this calibration routine, the following network between FILT and TST1 is required. TST2 must also be left floating. Detailed views are shown below.

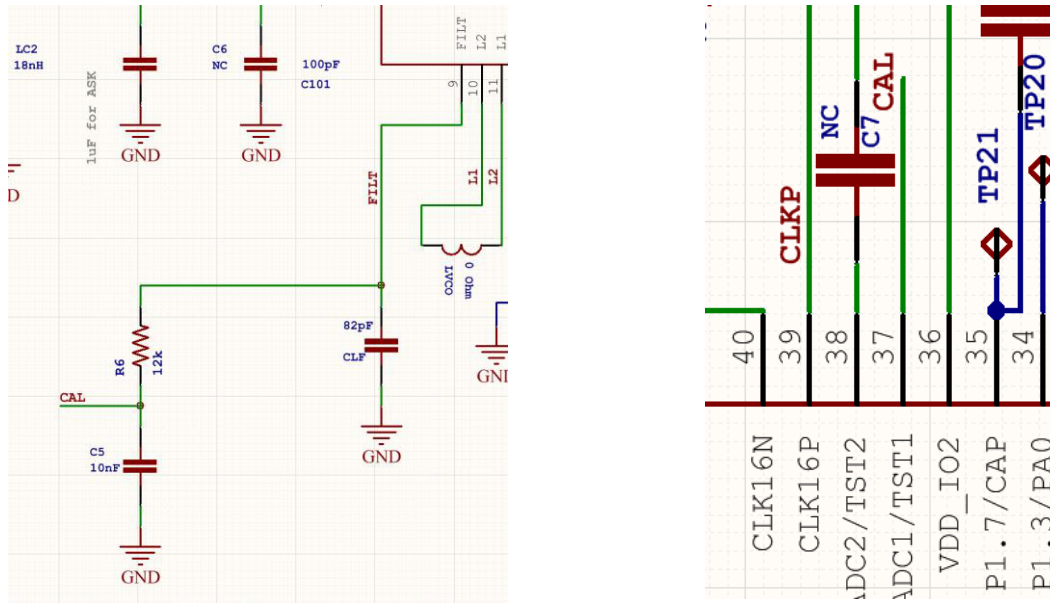


Figure 4.

## PCB Layout & Construction

Top Layer:

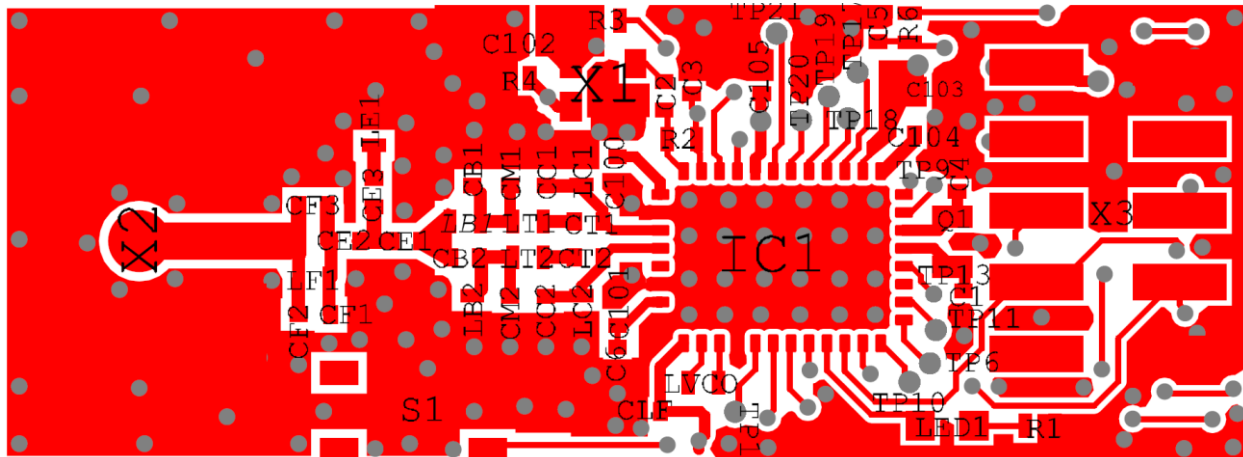


Figure 5. Top Layer

# TND6275/D

Bottom Layer (Mirrored to Reflect Physical View):

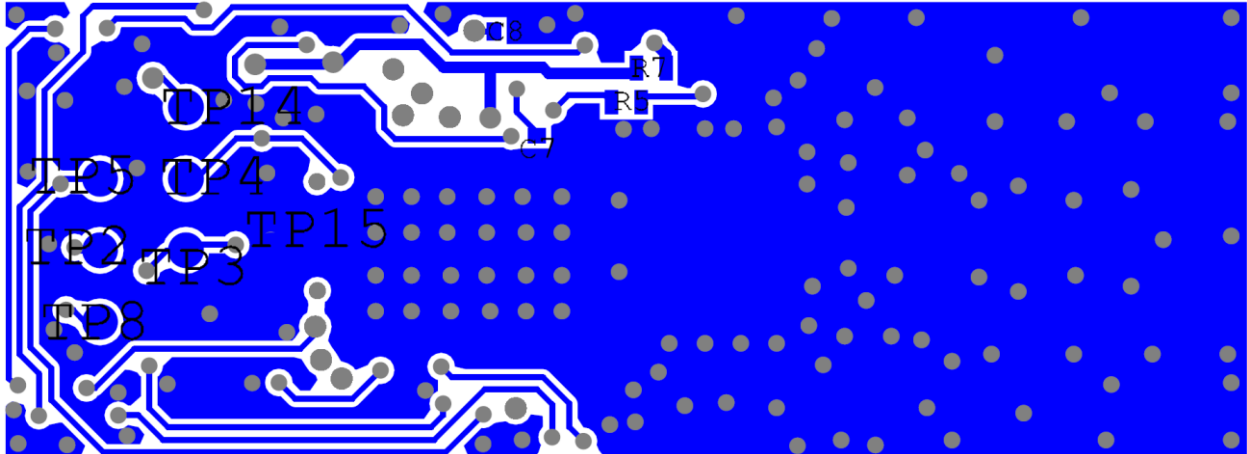









Figure 6. Bottom Layer (Mirrored to Reflect Physical View)

Layer Stack Up:

### Table 1. LAYER STACK UP

(Standard two layer PCB, FR4, 1 mm core, 35 μm (1 oz) copper. No impedance control di-electric instead.)

| Stack Up |   | Layer Stack   |               |       |     |
|----------|---|---------------|---------------|-------|-----|
| 1        |   | Top Overlay   |               |       |     |
|          |  | Top Solder    | Solder Resist | 0.024 | 3.5 |
|          |  | Top           | Copper        | 0.054 |     |
|          |  | Dielectric 1  | FR-4          | 1     | 4.6 |
|          |  | Bottom        | Copper        | 0.054 |     |
| 2        |  | Bottom Solder | Solder Resist | 0.024 | 3.5 |
|          |  |               |               |       |     |
| Height : |   |               |               | 1.156 |     |

# TND6275/D

## Bill of Materials

**Table 2. BILL OF MATERIALS**

| Designator                             | Quantity | Description                                       | Value                 | Tolerance | Footprint             | Manufacturer                     | Manufacturer Part Number |
|--|----------|---|-----------------------|-----------|-----------------------|----------------------------------|--------------------------|
| C1, C4                                 | 2        | CAP CER 8PF 25V NP0 0402                          | 8 pF                  | 0.25pF    | C0402                 | Murata Electronics               | GRM1555C1E8R0CA01D       |
| C2, C3, C5, C102                       | 4        | CAP CER 10000PF 25V X7R 0402                      | 10 nF                 | 10%       | C0402                 | Murata Electronics               | GRM155R71E103KA01D       |
| C6, C7, C8, CB1, CC1, CC2, CF3, R5, R7 | 9        |   | NC                    |           | C0402                 | Murata Electronics               |                          |
| C100, C101, C105                       | 3        | CAP CER 100PF 50V NP0 0402                        | 100 pF                | 5%        | C0402                 | Murata Electronics               | GRM1555C1H101JA01D       |
| C103                                   | 1        | CAP CER 4.7UF 6.3V X5R 0603                       | 4.7 $\mu$ F           | 10%       | C0603                 | Murata Electronics               | GRM188R60J475KE19J       |
| C104                                   | 1        |   | 100 nF                | 5%        | C0402                 | Murata Electronics               | GRM155R71C104JA88D       |
| CB2, CT1, CT2                          | 3        | CAP CER 2.7PF 50V NP0 0402                        | 2.7 pF                | 0.1pF     | C0402                 | Murata Electronics               | GRM1555C1H2R7BA01D       |
| CE1, CE2, R4, LVCO                     | 4        | RES SMD 0.0OHM JUMPER 1/16W 0402                  | 0 $\Omega$            | 5%        | R0402                 | Yaego                            | RC0402JR-070RL           |
| CE3                                    | 1        | CAP CER 0.9PF 50V NP0 0402                        | 0.9 pF                | 0.05pF    | C0402                 | Murata Electronics               | GRM1555C1HR90WA01D       |
| CF1, CF2                               | 2        | CAP CER 3.6PF 50V NP0 0402                        | 3.6 pF                | 0.1pF     | C0402                 | Murata Electronics               | GRM1555C1H3R6BA01D       |
| CLF                                    | 1        | CAP CER 82PF 50V NP0 0402                         | 82 pF                 | 2%        | C0402                 | Murata Electronics               | GRM1555C1H82GA01D        |
| CM1                                    | 1        | CAP CER 6.2PF 50V NP0 0402                        | 6.2 pF                | 0.1pF     | C0402                 | Murata Electronics               | GRM1555C1H6R2BA01D       |
| CM2                                    | 1        | CAP CER 3.6PF 50V NP0 0402                        | 3.6 pF                | 0.1pF     | C0402                 | Murata Electronics North America | GRM1555C1H3R6BA01D       |
| IC1                                    | 1        | SoC, RF, Range 27 - 1050 MHz                      |                       |           | QFN40                 | ON SEMICONDUCTOR                 | AXM0F243-1-TX40          |
| LB1, LB2                               | 2        | FIXED IND 11NH 500MA 140 MOHM                     | 11 nH                 | 2%        | L0402WW               | Murata Electronics               | LQW15AN11NG00D           |
| LC1, LC2                               | 2        | FIXED IND 18NH 370MA 270 MOHM                     | 18 nH                 | 2%        | L0402WW               | Murata Electronics               | LQW15AN18NG00D           |
| LE1                                    | 1        | FIXED IND 6.2NH 250MA 700 MOHM                    | 6.2 nH                | 2%        | L0402WW               | Murata Electronics               | LQW15AN6N2B00D           |
| LED1                                   | 1        |   | red                   |           | LED0603               | Murata Electronics               | LTST-C191KRKT            |
| LF1                                    | 1        | FIXED IND 8.2nH 500MA 170 MOHM                    | 8.2 nH                | 2%        | L0402WW               | Murata Electronics               | LQW15AN8N2G00D           |
| LT1, LT2                               | 2        | FIXED IND 15NH 460MA 160 MOHM                     | 15 nH                 | 2%        | L0402WW               | Murata Electronics               | LQW15AN15NG00D           |
| Q1                                     | 1        | 32.768KHz EXS00A-MU00788, NX2012SA                | 32.768 KHz Crystal    |           | TF20                  | Nihon Dempa Kogyo Co Ltd         | NX2012SA                 |
| R1                                     | 1        | RES SMD 220 OHM 5% 1/16W 0402                     | 220 $\Omega$          | 5%        | R0402                 | Yaego                            | RC0402JR-07220RL         |
| R2                                     | 1        | RES SMD 1K OHM 5% 1/16W 0402                      | 2.7 k $\Omega$        | 5%        | R0402                 | Yaego                            | RC0402JR-072K7L          |
| R3                                     | 1        | FERRITE CHIP 600 OHM 300MA 0402                   | BEAD 600 $\Omega$     |           | R0402                 | Murata Electronics               | BLM15AG601SN1D           |
| R6                                     | 1        | RES SMD 12K OHM 5% 1/16W 0402                     | 12 k $\Omega$         | 5%        | R0402                 | Yaego                            | RC0402JR-0712KL          |
| S1                                     | 1        | Tactile Switch SPST-NO Top Actuated Surface Mount | TASTER4-PAD-SMD-SMALL |           | TASTER_SMALL_SMD_4PAD | C&K                              | PTS810 SJK 250 SMTR LFS  |
| X1                                     | 1        |   | 48 MHz TCXO           |           | X2016                 | NDK (Nihon Dempa Kogyo Co. Ltd)  | NT2016SA 48 MHz END4910A |
| X2                                     | 1        | CONN SMA JACK STR 50OHM SMD                       | SMA-SMD               |           | SMA-SMD               | Linx Technologies Inc.           | CON SMA001-SMD-G         |
| X3                                     | 1        | CON_2X5 2MM-SMD_DEBUG                             | CON_2X5 2MM-SMD_DEBUG |           |                       | Harwin Inc.                      | M22-5320505              |

## FCC TITLE 47 PART 15 PRE-COMPLIANCE TESTING

### Overview of Regulations

US FCC title 47 part 15 regulates the use of radio frequency devices. The following sections are relevant to this context:

1. *US FCC 47 § 15.247* – Contains the regulations covering the frequency bands including 902 – 928 MHz
2. *US FCC 47 § 15.249* – Contains regulations for frequency bands including 902 – 928 MHz. This section allows for more flexibility in the modulation scheme and use case, but has a lower transmit power limit
3. *US FCC 47 § 15.205* – Defines the restricted bands of operation
4. *US FCC 47 § 15.209* – Defines the radiated field strength limits for emissions in the restricted bands of operation.

The purpose of this section is to detail the subset of tests that have been performed, along with their results, to demonstrate the compliance of a typical AXM0F243 902 – 928 MHz application with the FCC standard. For the context of this document, only the compliance with section 15.247 will be examined.

#### *Section 15.247 Summary*

Section 15.247 requires devices operating in the 902–928 MHz band to use either a frequency hopping or digital modulation scheme. Due to the wide bandwidth requirement for the specified digital modulation scheme, and the fact that the AXM0F243 is a narrow-band transceiver system-on-chip, the device will be tested using the frequency hopping requirements.

Compliance with the frequency hopping scheme is determined by the following specifications:

1. Frequency hopping systems shall have hopping channel carrier frequencies separated by a minimum of 25 kHz or the 20 dB bandwidth of the hopping channel, whichever is greater. [§ 15.247(a)(1)]
2. The system shall hop to channel frequencies that are selected at the system hopping rate from a pseudo randomly ordered list of hopping frequencies. Each frequency must be used equally on the average by each transmitter. [§ 15.247(a)(1)]

3. If the 20 dB bandwidth of the hopping channel is less than 250 kHz, the system shall use at least 50 hopping frequencies and the average time of occupancy on any frequency shall not be greater than 0.4 seconds within a 20 second period; if the 20 dB bandwidth of the hopping channel is 250 kHz or greater, the system shall use at least 25 hopping frequencies and the average time of occupancy on any frequency shall not be greater than 0.4 seconds within a 10 second period. The maximum allowed 20 dB bandwidth of the hopping channel is 500 kHz. [§ 15.247(a)(1)(i)]
4. The maximum peak conducted output power of the intentional radiator shall not exceed the following: 1 watt for systems employing at least 50 hopping channels; and, 0.25 watts for systems employing less than 50 hopping channels, but at least 25 hopping channels. [§ 15.247(a)(2)(b)(2)]
5. In any 100 kHz bandwidth outside the frequency band in which the spread spectrum or digitally modulated intentional radiator is operating, the radio frequency power that is produced by the intentional radiator shall be at least 20 dB below that in the 100 kHz bandwidth within the band that contains the highest level of the desired power, based on either an RF conducted or a radiated measurement, provided the transmitter demonstrates compliance with the peak conducted power limits. [§ 15.247 (d)]
6. Radiated emissions which fall in the restricted bands, as defined in § 15.205(a), must also comply with the radiated emission limits specified in § 15.209(a) [§ 15.247 (d)]

Because the AXM0F243 is a software-configurable transceiver system-on-chip, and ON Semiconductor has provided firmware libraries that give the developer control over operating frequency, compliance with the frequency hopping components of the FCC regulations is determined by the final application. For this reason, tests specifically related to the use of frequency hopping channels are omitted from this document. The regulatory tests detailed in this document are the following:

1. 20 dB Bandwidth
2. Peak Conducted Power
3. Spurious Conducted Emissions

The purpose of this section is to detail the subset of tests that have been performed, along with their results, to demonstrate the compliance of a typical AXM0F243 915 MHz application with the FCC regulatory standard. Note that the following is not a complete certification report. Several specifications required for certification were not applicable to the context of this design note and are not included.



**Test Setup & Equipment**

All tests were performed using conducted mode. Python scripts were used on the host PC to control the testing equipment, gather, and process the collected data. This section provides an overview of the test setup and equipment. Details pertaining to each test are given in the following section.

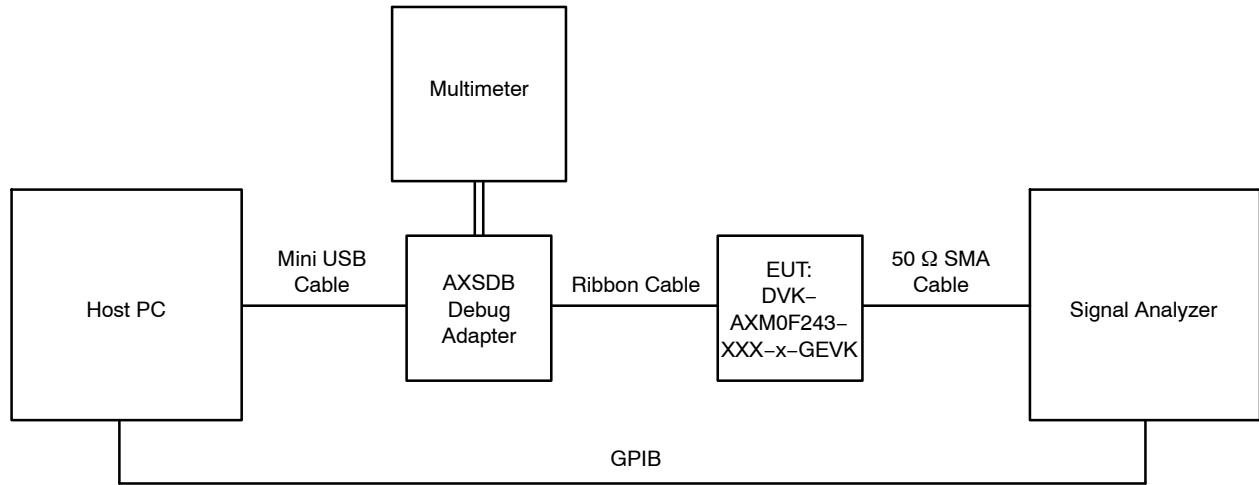
*Equipment Used:*

*Equipment Setup:*

The following block diagram and photo detail the setup for the transmitter tests:

**Table 3. EQUIPMENT USED**

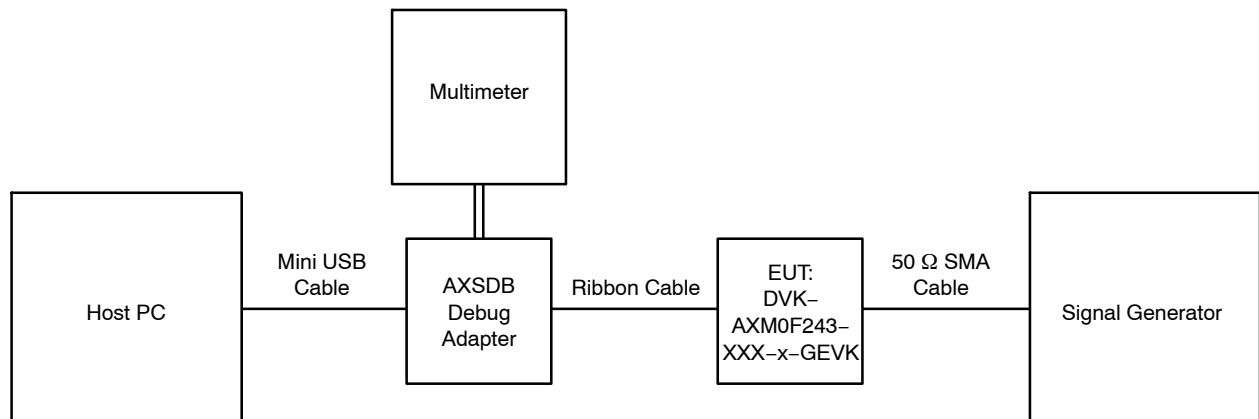
| Lab Equipment            | Type        | Manufacturer         |
|--------------------------|-------------|----------------------|
| Signal Analyzer 13.6 GHz | FSV-13      | Rhode & Schwartz     |
| Signal Generator         | SMU200A     | Rhode & Schwartz     |
| 6 1/2 Digit Multimeter   | 34461A      | Keysight             |
| USB / GPIB Interface     | GPIB-USB-HS | National Instruments |



**Figure 7.**

While US FCC title 47 part 15 only requires emission testing for the 902 to 928 MHz band, the sensitivity of the receiver was measured, and the following setup was used:

For sensitivity tests, the following test equipment setup was used:



**Figure 8.**

*Cable Loss*

The loss in the cable connecting the transmitter to the signal analyzer was measured to be 0.95 dBm. The results shown below are the values recorded directly from the measurement equipment, and do not account for the cable loss.

*Test Signal Description*

For each transmitter test, the EUT was programmed with AX–RadioLab to transmit a random stream of bits with the following physical layer parameters:

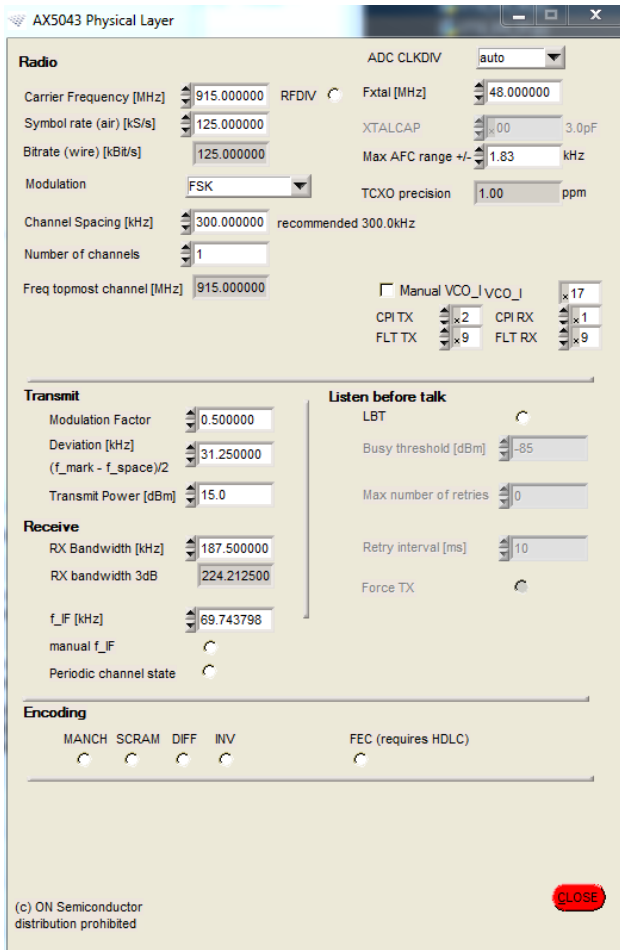


Figure 9.

*Temperature & Supply Voltage*

All tests were conducted at room temperature. For a full certification test, temperature and supply voltage extremes would need to be tested for most specifications.

**Test Results**

**20 dB Bandwidth**

This test measures the 20 dB bandwidth of a modulated signal, which is used to determine the required number of frequency hopping channels as per § 15.247(a)(1)(i). The measurement parameters used are shown below:

Table 4.

| Measurement Parameters |               |
|------------------------|---------------|
| Detector:              | Positive Peak |
| Sweep Time:            | Auto          |
| Resolution Bandwidth:  | 5 kHz         |
| Video Bandwidth:       | 15 kHz        |
| Span:                  | 1 MHz         |
| Trace Mode:            | Max Hold      |

*Results:*

As shown in the spectrum plot below, the measured 20 dB bandwidth of the given modulated signal is 169.6 kHz. This signal represents a data rate toward the upper limit of the capability of the narrowband AXM0F243, thus in most applications, 50 frequency hopping channels should be used.

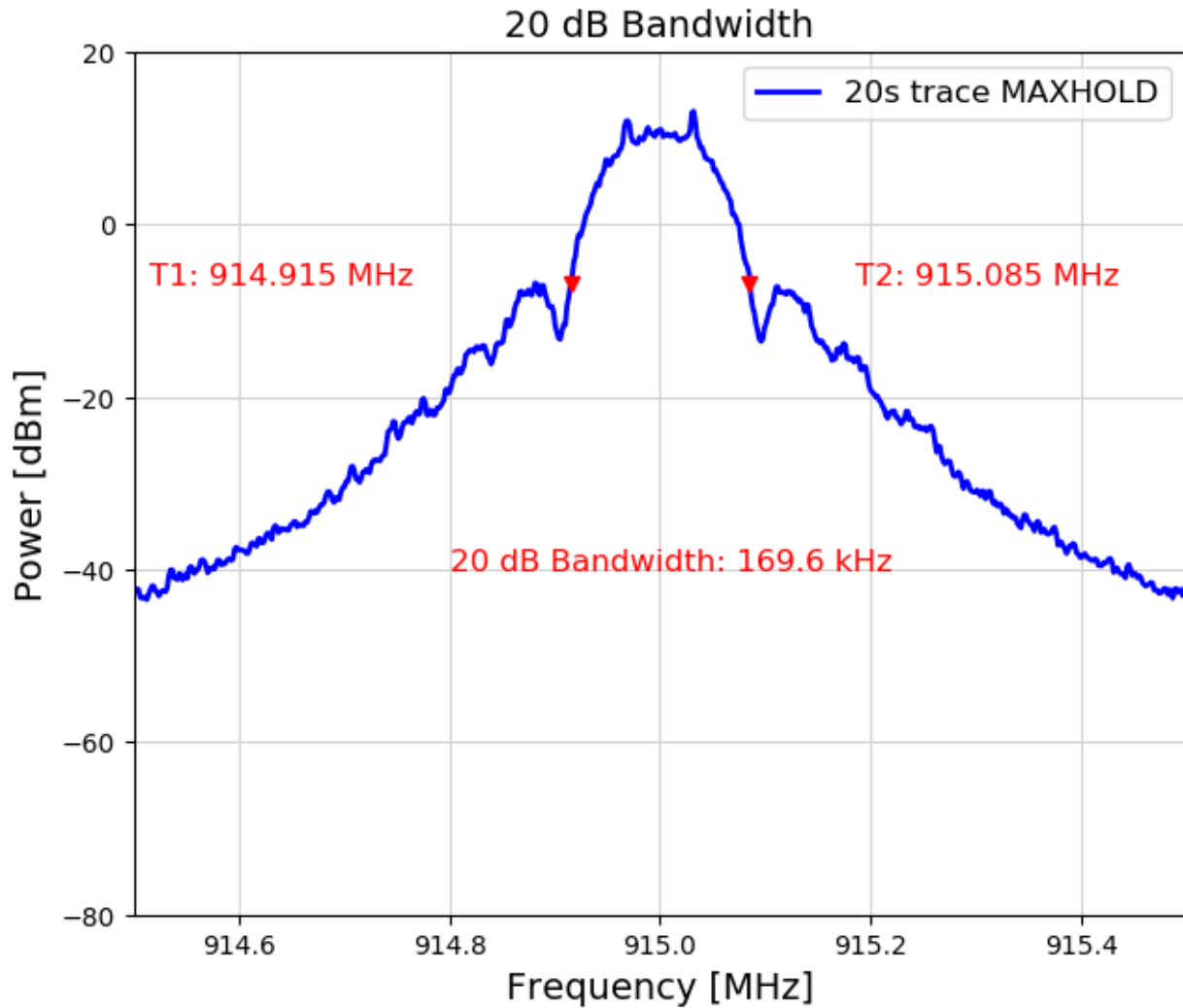


Figure 10.

**Peak Conducted Power**

*Description:*

This section demonstrates the procedure for measuring the peak output power. The limit defined in § 15.247(a)(2)(b)(2) is 1 watt, or 30 dBm.

*Results:*

The measured maximum output power of DVK-AXM0F243-915 (shown below) is well below the limit. An external PA can be utilized to increase the output power.

**Table 5.**

| Measurement Parameters |               |
|------------------------|---------------|
| Detector:              | Positive Peak |
| Sweep Time:            | Auto          |
| Resolution Bandwidth:  | 200 kHz       |
| Video Bandwidth:       | 200 kHz       |
| Span:                  | 1 MHz         |
| Trace Mode:            | Max Hold      |

# TND6275/D

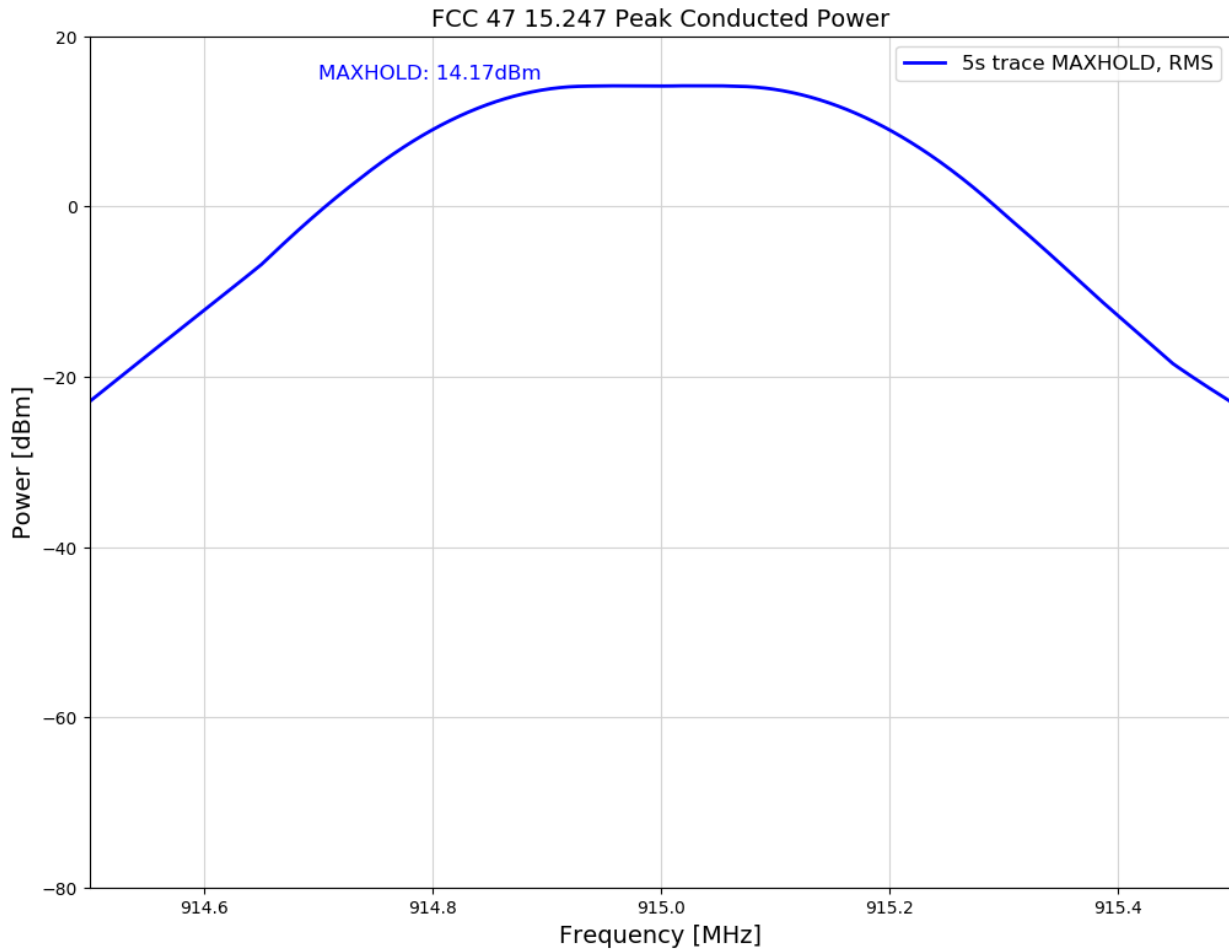


Figure 11.

## Spurious Conducted Emissions

### Description:

This test measures the output spectrum and verifies that the spurious emissions of the given modulated signal do not exceed the defined limits.

Table 6.

| Measurement Parameters |                 |
|------------------------|-----------------|
| Detector:              | Positive Peak   |
| Sweep Time:            | Auto            |
| Resolution Bandwidth:  | 100 kHz         |
| Video Bandwidth:       | 300 kHz         |
| Span:                  | See Plots below |
| Test Signal:           | Max Hold        |

### Results:

The output spectrum plot is shown below, and is masked with the restricted bands and corresponding power limits. The power limits were calculated from the field strength limits given by § 15.205(a) and § 15.209(a) in the following manner:

$$P_{dBm} = 10 \log_{10} \left( \frac{P}{0.001} \right) \quad (\text{eq. 1})$$

Where

$$P = 0.3 (E \cdot 1 \cdot 10^{-6})^2 \quad (\text{eq. 2})$$

P is the conducted limit in Watts,  $P_{dBm}$  is the conducted limit in dBm, and E is the given field strength limit, given in  $\mu\text{V/m}$ .

# TND6275/D

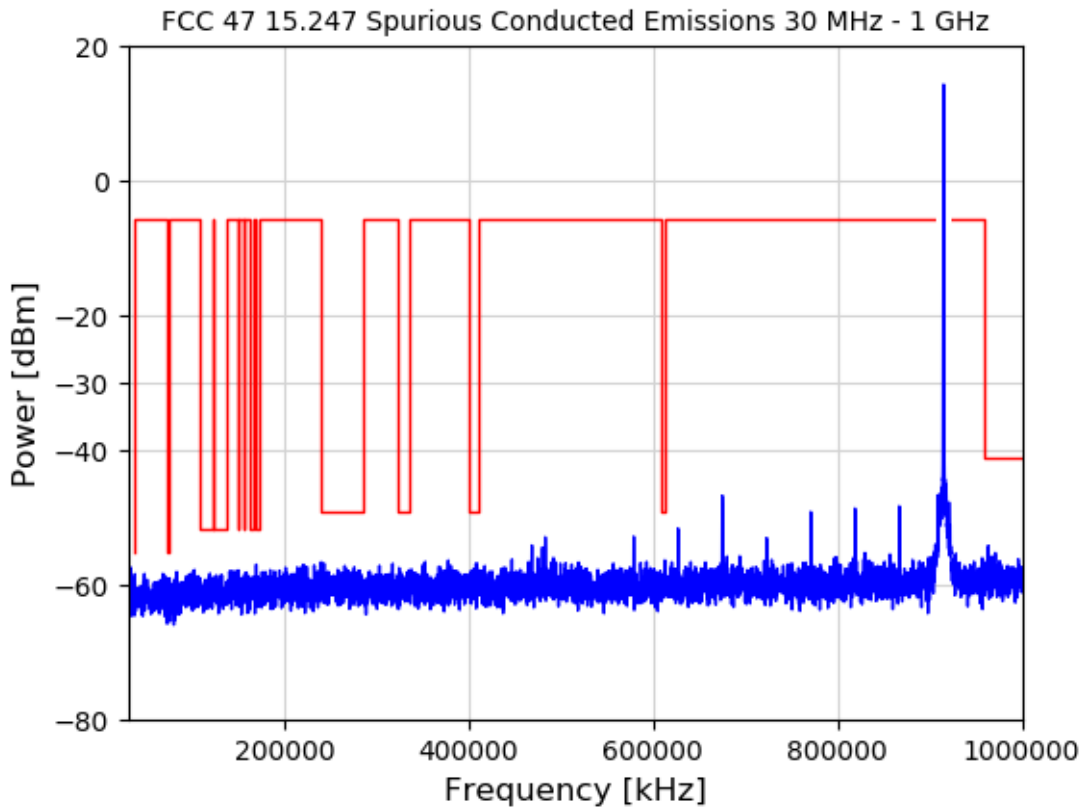


Figure 12.

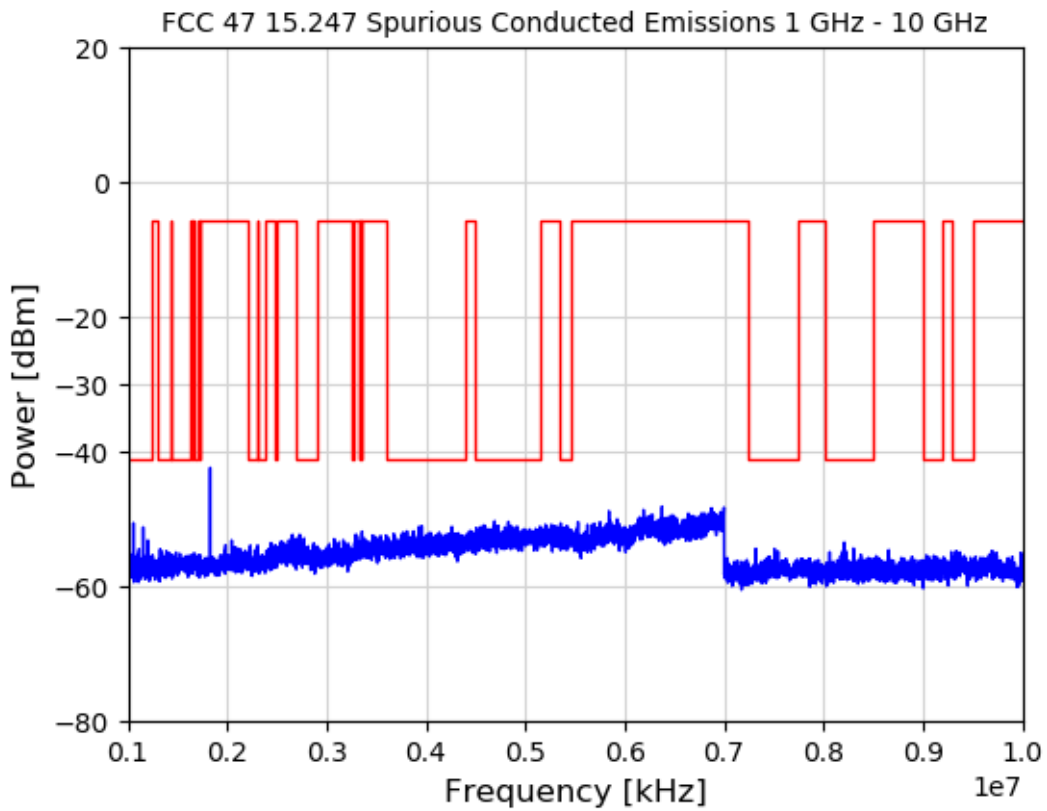


Figure 13.

## ADDITIONAL PERFORMANCE TESTS

### TX Power vs. Current Consumption

The given signal was output from the device. Power level was measured using the spectrum analyzer. Current was measured with the multimeter by probing jumper #3 on the AXDBG debug adapter. Current values represent the consumption by the AXM0F243 SoC, and consist of the combined consumption for both the microcontroller and radio cores. Note that the output power amplifier and match network have been optimized for maximum TX power output. The component values can be modified to optimize power efficiency at low TX output power levels. The measured current consumption is shown in the table below:

**Table 7.**

| Measured TX Power (dBm) | TX Power w/ Cable Loss (dBm) | Measured Current Consumption (mA) |
|-------------------------|------------------------------|-----------------------------------|
| 14.72                   | 15.67                        | 80.2                              |
| 6.6                     | 7.55                         | 42.5                              |
| -0.8                    | 0.15                         | 29.4                              |
| -11.2                   | -10.25                       | 23.3                              |

### RX Sensitivity

The receiver sensitivity was measured with the test setup described previously. The EUT was configured to receive a FSK 1010 signal from the generator and send the calculated BER to the host PC via UART. The power of the modulated signal from Generator A was reduced until a BER of 0.001 was observed. The sensitivity values are reported in the table below. The RX current value is also shown below, which includes the current for the radio, MCU, and LED.

**Table 8.**

| 915 MHz FSK Sensitivity |                            |                                 |              |
|-------------------------|----------------------------|---------------------------------|--------------|
| Datarate (kbps)         | Measured Sensitivity (dBm) | Sensitivity w/ Cable Loss (dBm) | Current (mA) |
| 1                       | -121                       | -121.95                         | 23.79        |
| 10                      | -114                       | -114.95                         | 23.3         |
| 100                     | -103                       | -103.95                         | 23.3         |
| 125                     | -101                       | -101.95                         | 24.2         |

## REFERENCES & LINKS

### ON Semiconductor Resources


1. AXM0F243 Device Page:  
<https://www.onsemi.com/PowerSolutions/product.do?id=AXM0F243>

### FCC

1. US FCC 47 § 15.247:  
<https://www.govinfo.gov/content/pkg/CFR-2013-title47-vol1/pdf/CFR-2013-title47-vol1-sec15-247.pdf>
2. US FCC 47 § 15.249:  
<https://www.govinfo.gov/content/pkg/CFR-2009-title47-vol1/pdf/CFR-2009-title47-vol1-sec15-249.pdf>
3. US FCC 47 § 15.205:  
<https://www.govinfo.gov/content/pkg/CFR-2001-title47-vol1/pdf/CFR-2001-title47-vol1-sec15-205.pdf>
4. US FCC 47 § 15.209:  
<https://www.govinfo.gov/content/pkg/CFR-2002-title47-vol1/pdf/CFR-2002-title47-vol1-sec15-209.pdf>
5. Test procedures for measuring Digital Transmission System (DTS):  
<https://apps.fcc.gov/oetcf/kdb/forms/FTSSearchResultPage.cfm?switch=P&id=21124>
6. ANSI C63.10:  
[https://standards.ieee.org/standard/C63\\_10-2013.html](https://standards.ieee.org/standard/C63_10-2013.html)

### Class-E Amplifier and Output Network Design

1. Load Network Design Techniques for Class E RF and Microwave Amplifiers:  
<http://rfcafe-com.secure38.ezhostingserver.com/references/articles/Load-Network-Design-Techniques-for-Class-E-RF-and-Microwave-Amplifier.pdf>
2. Balun component calculator:  
<http://analog.intgckts.com/impedance-matching/lumped-lc-balun/>

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